

Supplementary Information for

**Construction of crossed heterojunction from p-ZnTe and n-CdSe
nanoribbons and their photoresponse properties**

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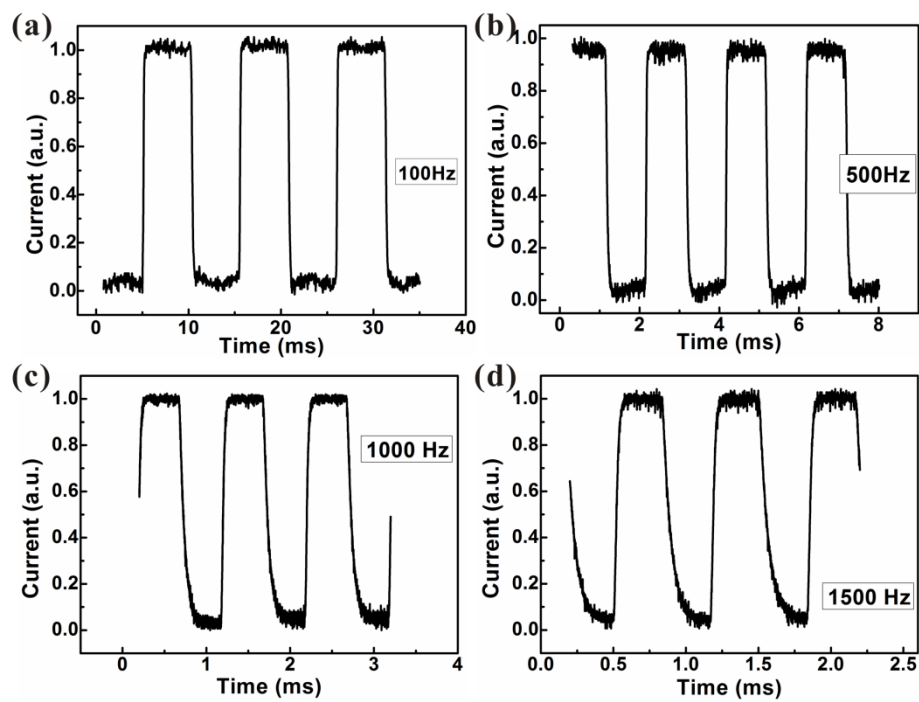


Fig. S1 Photoresponse characteristics of the HD device for pulsed light irradiation at frequencies of (a) 100 Hz, (b) 500 Hz, (c) 1000 Hz and (d) 1500 Hz.

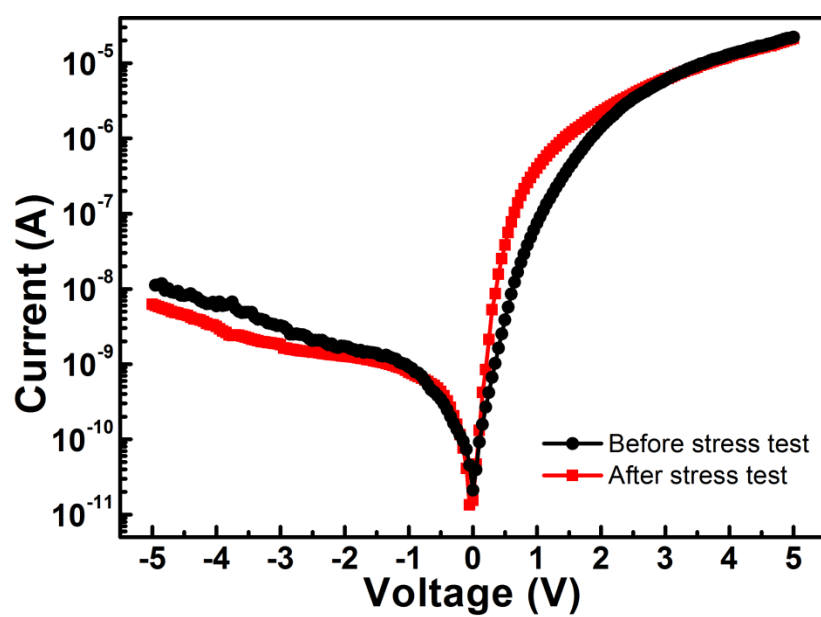


Fig. S2 I-V curves of the HD device measured before and after stress test.